## D44H Series (NPN), D45H Series (PNP)

## **Complementary Silicon Power Transistors**

These series of plastic, silicon NPN and PNP power transistors can be used as general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

#### **Features**

- Low Collector-Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

| Rating  | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Collector–Emitter Voltage<br>D44H8, D45H8<br>D44H11, D45H11             | V <sub>CEO</sub>                  | 60<br>80    | Vdc  |
| Emitter Base Voltage  | V <sub>EB</sub>                   | 5.0         | Vdc  |
| Collector Current – Continuous  | I <sub>C</sub>                    | 10          | Adc  |
| Collector Current – Peak (Note 1)                                       | I <sub>CM</sub>                   | 20          | Adc  |
| Total Power Dissipation @ T <sub>C</sub> = 25°C @ T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 70<br>2.0   | W    |
| Operating and Storage Junction<br>Temperature Range                     | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

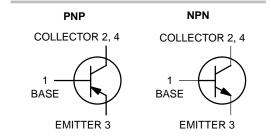
| Characteristic  | Symbol          | Max  | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction-to-Case  | $R_{\theta JC}$ | 1.8  | °C/W |
| Thermal Resistance, Junction-to-Ambient                                       | $R_{\theta JA}$ | 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds | TL              | 275  | °C   |



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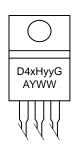
www.onsemi.com

# 10 AMP COMPLEMENTARY SILICON POWER TRANSISTORS 60, 80 VOLTS





MARKING DIAGRAM



D4xHyy = Device Code

x = 4 or 5

yy = 8 or 11

A = Assembly Location

TO-220

**CASE 221A** 

STYLE 1

Y = Year WW = Work Week

= Pb-Free Package

## ORDERING INFORMATION

| Device  | Package             | Shipping      |
|---------|---------------------|---------------|
| D44H8G  | TO-220<br>(Pb-Free) | 50 Units/Rail |
| D44H11G | TO-220<br>(Pb-Free) | 50 Units/Rail |
| D45H8G  | TO-220<br>(Pb-Free) | 50 Units/Rail |
| D45H11G | TO-220<br>(Pb-Free) | 50 Units/Rail |

<sup>1.</sup> Pulse Width  $\leq$  6.0 ms, Duty Cycle  $\leq$  50%.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## D44H Series (NPN), D45H Series (PNP)

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25$ °C unless otherwise noted)

| Characteristic   | Symbol                         | Min                             | Тур           | Max          | Unit         |     |
|--|--------------------------------|---------------------------------|---------------|--------------|--------------|-----|
| OFF CHARACTERISTICS  |                                | <del>'</del>                    |               | <del>!</del> | <del>!</del> |     |
| Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0 Adc)    | D44H8, D45H8<br>D44H11, D45H11 | V <sub>CEO(sus)</sub>           | 60<br>80      | -<br>-       | _<br>_       | Vdc |
| Collector Cutoff Current ( $V_{CE}$ = Rated $V_{CEO}$ , $V_{BE}$                           | = 0)                           | I <sub>CES</sub>                | _             | -            | 10           | μΑ  |
| Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc)   |                                | I <sub>EBO</sub>                | -             | -            | 10           | μΑ  |
| ON CHARACTERISTICS   |                                |                                 |               | •            |              | •   |
| DC Current Gain  |                                | h <sub>FE</sub>                 | 60<br>40      | -<br>-       | -<br>-       | -   |
| Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc)  |                                | V <sub>CE(sat)</sub>            | _             | -            | 1.0          | Vdc |
| Base–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc)       |                                | V <sub>BE(sat)</sub>            | -             | -            | 1.5          | Vdc |
| DYNAMIC CHARACTERISTICS  |                                |                                 |               |              |              |     |
| Collector Capacitance<br>(V <sub>CB</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)           | D44H Series<br>D45H Series     | C <sub>cb</sub>                 | <u>-</u><br>- | 90<br>160    | _<br>_       | pF  |
| Gain Bandwidth Product<br>(I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz) | D44H Series<br>D45H Series     | f <sub>T</sub>                  | <u>-</u><br>- | 50<br>40     | _<br>_       | MHz |
| SWITCHING TIMES  |                                |                                 |               |              |              |     |
| Delay and Rise Times<br>(I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = 0.5 Adc)              | D44H Series<br>D45H Series     | t <sub>d</sub> + t <sub>r</sub> |               | 300<br>135   | _<br>_       | ns  |
| Storage Time $(I_C = 5.0 \text{ Adc}, I_{B1} = I_{B2} = 0.5 \text{ Adc})$                  | D44H Series<br>D45H Series     | t <sub>s</sub>                  | -<br>-        | 500<br>500   | _<br>_       | ns  |
| Fall Time<br>(I <sub>C</sub> = 5.0 Adc, I <sub>B1</sub> = 102 = 0.5 Adc)                   | D44H Series<br>D45H Series     | t <sub>f</sub>                  | -             | 140<br>100   | _<br>_       | ns  |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## D44H Series (NPN), D45H Series (PNP)

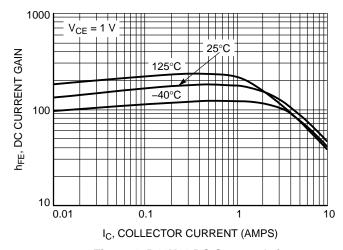


Figure 1. D44H11 DC Current Gain

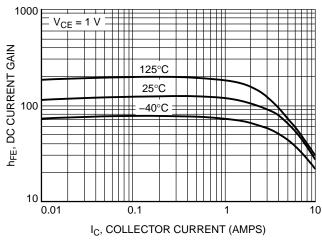


Figure 2. D45H11 DC Current Gain

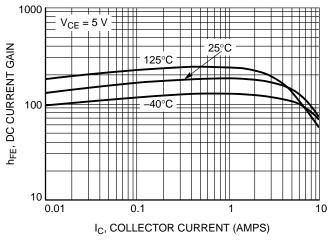


Figure 3. D44H11 DC Current Gain

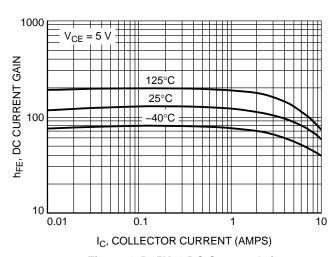


Figure 4. D45H11 DC Current Gain

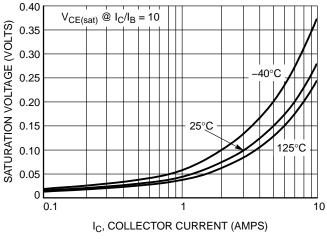


Figure 5. D44H11 ON-Voltage

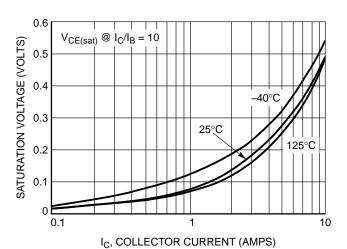


Figure 6. D45H11 ON-Voltage

## D44H Series (NPN), D45H Series (PNP)

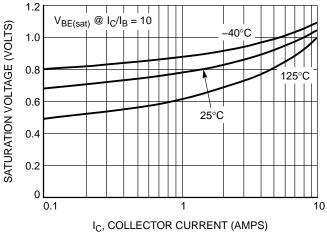


Figure 7. D44H11 ON-Voltage

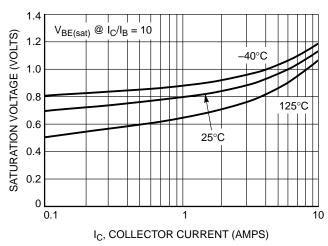


Figure 8. D45H11 ON-Voltage

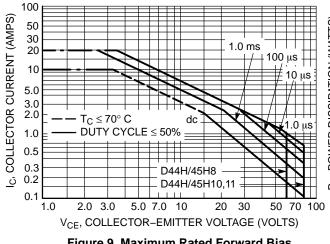


Figure 9. Maximum Rated Forward Bias Safe Operating Area

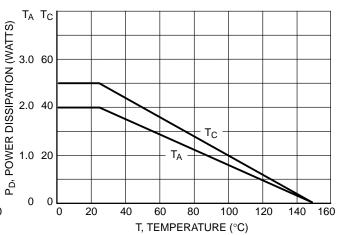


Figure 10. Power Derating

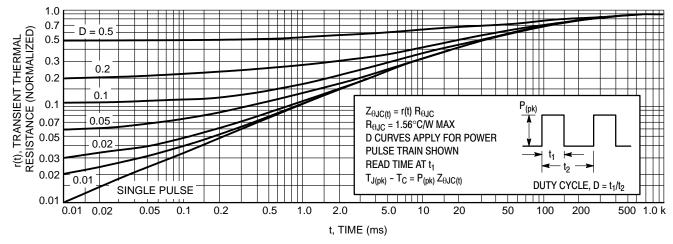
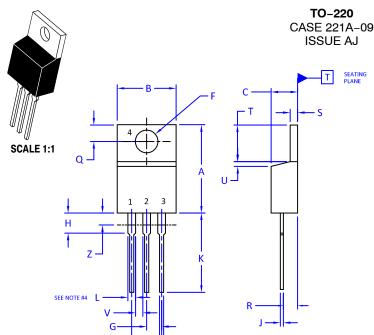


Figure 11. Thermal Response

## **MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS**





## **DATE 05 NOV 2019**

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES

NOTES:

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

|     | INCHES |       | MILLIMI | ETERS |
|-----|--------|-------|---------|-------|
| DIM | MIN.   | MAX.  | MIN.    | MAX.  |
| Α   | 0.570  | 0.620 | 14.48   | 15.75 |
| В   | 0.380  | 0.415 | 9.66    | 10.53 |
| С   | 0.160  | 0.190 | 4.07    | 4.83  |
| D   | 0.025  | 0.038 | 0.64    | 0.96  |
| F   | 0.142  | 0.161 | 3.60    | 4.09  |
| G   | 0.095  | 0.105 | 2.42    | 2.66  |
| Н   | 0.110  | 0.161 | 2.80    | 4.10  |
| J   | 0.014  | 0.024 | 0.36    | 0.61  |
| К   | 0.500  | 0.562 | 12.70   | 14.27 |
| L   | 0.045  | 0.060 | 1.15    | 1.52  |
| N   | 0.190  | 0.210 | 4.83    | 5.33  |
| Q   | 0.100  | 0.120 | 2.54    | 3.04  |
| R   | 0.080  | 0.110 | 2.04    | 2.79  |
| S   | 0.045  | 0.055 | 1.15    | 1.41  |
| Т   | 0.235  | 0.255 | 5.97    | 6.47  |
| U   | 0.000  | 0.050 | 0.00    | 1.27  |
| V   | 0.045  |       | 1.15    |       |
| Z   |        | 0.080 |         | 2.04  |

| STYLE 1: |           | STYLE 2:  |           | STYLE 3:  |         | STYLE 4: |                    |
|----------|-----------|-----------|-----------|-----------|---------|----------|--------------------|
| PIN 1.   | BASE      | PIN 1.    | BASE      | PIN 1.    | CATHODE | PIN 1.   | MAIN TERMINAL 1    |
| 2.       | COLLECTOR | 2.        | EMITTER   | 2.        | ANODE   | 2.       | MAIN TERMINAL 2    |
| 3.       | EMITTER   | 3.        | COLLECTOR | 3.        | GATE    | 3.       | GATE               |
| 4.       | COLLECTOR | 4.        | EMITTER   | 4.        | ANODE   | 4.       | MAIN TERMINAL 2    |
| STYLE 5: |           | STYLE 6:  |           | STYLE 7:  |         | STYLE 8: |                    |
| PIN 1.   | GATE      | PIN 1.    | ANODE     | PIN 1.    | CATHODE | PIN 1.   | CATHODE            |
| 2.       | DRAIN     | 2.        | CATHODE   | 2.        | ANODE   | 2.       | ANODE              |
| 3.       | SOURCE    | 3.        | ANODE     | 3.        | CATHODE | 3.       | EXTERNAL TRIP/DELA |
| 4.       | DRAIN     | 4.        | CATHODE   | 4.        | ANODE   | 4.       | ANODE              |
| STYLE 9: |           | STYLE 10: |           | STYLE 11: |         | STYLE 12 | :                  |
| PIN 1.   | GATE      | PIN 1.    | GATE      | PIN 1.    | DRAIN   | PIN 1.   | MAIN TERMINAL 1    |
| 2.       | COLLECTOR | 2.        | SOURCE    | 2.        | SOURCE  | 2.       | MAIN TERMINAL 2    |
| 3.       | EMITTER   | 3.        | DRAIN     | 3.        | GATE    | 3.       | GATE               |
| 4.       | COLLECTOR | 4.        | SOURCE    | 4.        | SOURCE  | 4.       | NOT CONNECTED      |
|          |           |           |           |           |         |          |                    |

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